



5/A 1.28.98 Caron

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Vora Art Unit: 2512

Examiner: GIORDANA

Serial No. 08/654,760

Filed: 5/29/96

For: VERTICALLY INTEGRATED FLASH EEPROM FOR GREATER DENSITY AND LOWER COST

**Box Amendment** 

Honorable Commissioner of Patents and Trademarks Washington, D.C. 20231

Morgan Hill, California November 15, 1997

## **AMENDMENT**

Dear Sir:

In response to the Office Action mailed , please amend the above identified case as follows.

## IN THE DRAWINGS

Enclosed is a markup of Figures 3 and 4 for approval by the Examiner.

### IN THE SPECIFICATION

At page 1, line 11, delete "appliction", and substitute --application--.

### IN THE CLAIMS

1. (Amended) A nonvolatile memory cell/array comprised of a plurality of EEPROM

memory cells, each cell comprising:

a semiconductor substrate;

a vertical MOS transistor formed by alternating N-type and P-type doped layers

V&F-001 Amend 11/97

1